Birla Institute of Technology and Science, Pilani ECE/EEE / INSTR F244 F244 Microelectronic Circuits Comprehensive Examination, II Semester, 2022-2023

<u>Note----(Specify your assumptions clearly.</u>)

 $\begin{array}{lll} \textit{Unless given specifically} \\ \textit{Take -- } & V_{\rm DD} = V_{\rm CC} = 3.3 \, \mathrm{V}, \\ \textit{For NMOS device} & \mu_n Cox = 140 \, \mu A/V^2, \, V_T = 0.7 \, \, \mathrm{V}, \, \lambda = 0.1 \, \, \mathrm{V}^{-1}, \ \text{Vov=0.2 V} \\ \textit{For PMOS device} & \mu_p Cox = 40 \, \, \mu A/V^2, \, V_T = - \, 0.7 \, \, \mathrm{V}, \, \lambda = \, 0.1 \, \, \mathrm{V}^{-1}, \ \text{Vov=0.2 V} \\ \textit{For NPN/ PNP device} & \beta = 100 \, \, \mathrm{V}, \, V_{\rm CE,SAT} = 0.2 \, \mathrm{V}, \, V_A = 100 \, \mathrm{V}, \, \mathrm{KT/q} = 25 \, \mathrm{mV}(\text{at room temp.}), \, \mathrm{Is} = 10^{-14} \, \mathrm{A}, \, \mathrm{V_{BE,ON}} = 0.6 \, \mathrm{V}, \, \alpha \approx 1 \\ \textit{NOTE:} \end{array}$ 

If not specified in question -----

- Ignore  $\gamma$ ,  $\lambda$  in drain current equation. Bulk of nmos connected to ground and bulk of pmos connected to V<sub>dd</sub>.
- Unless specified, assume all MOSFETs are biased in the active region All symbols have the usual meaning.

\_\_\_\_\_

# Answer all the sub-parts of a question in sequence and one place only. Clearly show the procedure used to arrive at the answer for full credit. Report the answers with proper units.

Q 1. Consider the Amplifier circuit given in Fig.1. Following values

are given for the circuit:  $R_F = 100 \text{ K}\Omega$ ,  $R_D = 5 \text{ K}\Omega$ ,  $R_L = 5 \text{ K}\Omega$ ,  $K_n' = 20 \mu A/V^2$ ,  $L = 10 \mu m$ ,  $W = 200 \mu m$ ,  $V_A = 100 \text{ V}$ ,

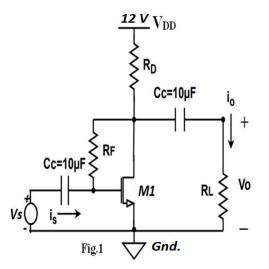
 $V_t = 2 V$ . Assume all the capacitors are open for DC bias and short

at given signal frequency.

Determine the following:

Time: 60 minutes

- *a*) DC Operating point  $(I_{DQ}, V_{GSQ}, V_{DSQ})$
- b) Input Impedance and Output Impedance
- c) Voltage gain and Current gain



Q 2. (A) Consider the circuit of Fig. 2

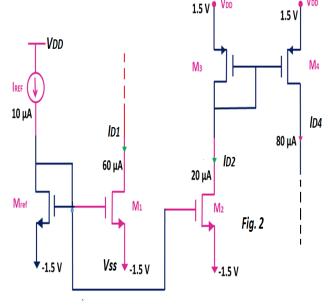
Given,  $|V_{tn}| = |V_{tp}| = 0.6V$ ,  $\mu_n C_{ox} = 200 \,\mu A/V^2$ ,  $\mu_p C_{ox} = 60 \,\mu A/V^2$ . ---The channel length of all transistors=1  $\mu$ m. ---The minimum allowed drain voltage at M<sub>1</sub> and M<sub>4</sub> are -1.3V and 1.3V, respectively.

#### Find the widths of M<sub>1</sub>, M<sub>2</sub>, M<sub>4</sub>.

**Q2(B)** For a p-channel long MOSFET, threshold Voltage (V<sub>T</sub>) = -1 V, W = 20  $\mu$ m, L = 2  $\mu$ m. Given,  $\mu_p = 200 \text{ cm}^2/\text{V-s}$ , C<sub>ox</sub> = 3.5 × 10<sup>-7</sup> F/cm<sup>2</sup>. The source and body are connected to the ground.

Calculate the drain current for following conditions----

a) at  $V_G = -4 V$ ,  $V_D = -1 V$ . b) at  $V_G = -3 V$ ,  $V_D = -3 V$ .



[ 20 marks]

[20 marks]

Total Marks: 70

### Part-B (Open Book)

### Use data/parameters given in part (A)

NOTE-- There are **FOUR** questions. Answer all the sub-parts of a question in sequence and one place only. Clearly show the procedure used to arrive at the answer for full credit. Report the answers with proper units.

**Q1.** Consider the circuit shown in Fig 1., where the applied input

voltages are:

 $vin_1 = 5mv sinwt + 1.4V$  and  $vin_2 = 10mv sinwt + 1.4V$ .

--Transistors M1, M2 has Vov= 0.2 V. The value of Iss=90 uA

-- Iss is implemented with basic current mirror with large Rss.

--Assume perfect matching of transistors,

Time: 2 hrs.

--Resistors with  $R_{D1} = R_{D2} = R_D = 40 \text{ K}\Omega$ .

- a) Now, analyze the given circuit and calculate the dc voltage at nodes P and X.
- b) Calculate the differential mode gain, (Adm), for the given circuit.
- c) Determine common mode component of each input signal (vin1 and vin2) and differential mode component of each input signal (vin1 and vin2)
- d) Now, determine a.c value of total **Vout** tapped between vout1 & vout2 nodes. (Vout = vout1-vout2).
- e) Finally, draw a labelled plot for Vout (t) vs. time. (show both DC and AC components)

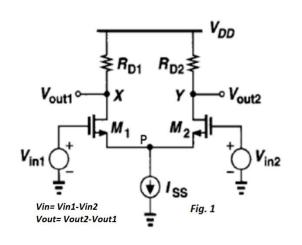
[19 marks]

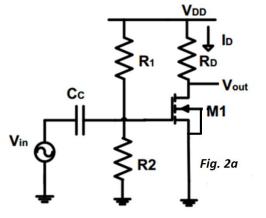
- Q2. (A) Consider Fig 2a Given: W/L= 25, R<sub>1</sub> ll R<sub>2</sub> = 100k $\Omega$ , V<sub>TN</sub> = 1V, I<sub>DQ</sub> = 2mA, R<sub>D</sub> = 2.5k $\Omega$ , Vdd=12 V
- a) Draw the Load line of the given circuit and mark the maximum value of I<sub>D</sub> and V<sub>DS</sub> on the x-axis and y-axis, respectively.
- **b**) Find the value of  $V_{DSQ}$  and  $V_{GSQ}$  in such a way that the Q point is in the **middle** of the saturation (active) region.
- c) Find the value of  $\mathbf{R}_1$  and  $\mathbf{R}_2$ .

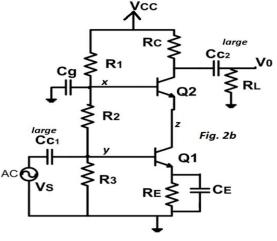
Q2 (B) Consider Fig. 2b of cascode amplifier, Vdd/ Vcc=12 V

- d) Sketch and label the small-signal (low frequency) equivalent model for the given amplifier. (Assuming  $\lambda \Rightarrow 0$ )
- e) Find out the gain expression of the above amplifier.Compare the gain expression with a conventionalCommon emitter/base amplifier.

[Total 19 marks]







- Q3. Consider the circuit given below in Fig. 3.
- The Following parameters are given:

$$\begin{split} V_{ov} &= 0.2V, \, \lambda = 0.01V^{\text{-1}}, \ C_{gs(1,2)} = 10pF, \\ C_{gd(1,2)} &= 1pF, \, C_{db(1,2)=}2pF, \, C_{sb(1,2)} = 2pF \text{ and} \\ R_s << 1/g_m \end{split}$$

**Ignore** the capacitances of the basic current mirror current source M3

- a) Sketch and label the high frequency model of the amplifier.
- b) Identify the number of dominant poles and zeros of the amplifier.
- c) Calculate the frequency (in rad./s) of the dominant poles and zeros of the amplifier.
- d) Calculate the **phase** of the amplifier at  $\omega = 10$ K rad/s.
- e) Plot and label the **Bode magnitude response** of the amplifier (Use corner plot) qualitatively. Mark the values of low frequency voltage gain (**vout/vin**) and the dominant poles and zeros along with UGB on it.
- **f**) Calculate the unity gain frequency (**UGB in rad./s**)

## [17 marks]

- Q4. Consider the circuit given in **Fig. 4**.
- The bias current I5=25uA, Iss=200 uA.

For all devices take, V(overdrive) = 0.2 V,

 $\lambda$ =0.01 V<sup>-1</sup> Assume load capacitance at output is

 $C_L=1nF$ , Rsig is small

 $R_p=1K\Omega$ ,  $R_F=1M\Omega$ ,  $R_S=1K\Omega$ 

Neglect body effect in calculations.

- a) Identify the type of feedback in this amplifier.
  Hence determine type of input and output signal of feedback amplifier
- b) Determine the **open loop** parameters  $A_o$ ,  $R_{out}$  at low frequency
- c) Determine closed loop parameters:  $A_{0f}$ ,  $R_{inf}$ ,  $R_{outf}$ , feedback factor ( $\beta$ ) at low frequency
- d) Assuming that **output node pole** is dominant pole, determine the **-3dB frequency**, and **UGB** (unity gain bandwidth) in both **open loop** and **closed loop** condition.
- Also determine gain-crossover frequency (Gx) in closed loop mode.

